S/N Unknown **PATENT**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Gary R. Gilliam	Examiner: Unknown	
Serial No.:	Unknown	Group Art Unit: Unknown	
Filed:	Herewith	Docket: 303.221US4	
Title:	ON-CHIP SUBSTRATE REGULATOR TEST MODE		

PRELIMINARY AMENDMENT

BOX PATENT APPLICATON
Commissioner for Patents
Washington, D.C. 20231

Sir:

When the above-identified patent application is taken up for consideration, please amend the application as follows:

IN THE SPECIFICATION

On page 1, line 3, before the heading "Field of the Invention," insert the following paragraph:

Cross Reference to Related Application(s)

This application is a division of U.S. Application No. 09/065,139, filed on April 23, 1998, which is a division of U.S. Application No. 08/520,818, filed on August 30, 1995, now issued as U.S. Patent No. 5,880,593, the specifications of which are hereby incorporated by reference.

Please substitute the following paragraphs of the Specification with the paragraphs in the appendix entitled "Clean Version of Specification Paragraphs." Following are marked-up versions of the amended paragraphs showing specific changes:

The paragraph beginning on page 4, line 19, is amended as follows:

For example, in Figure 1, the non-test condition of EN1 may be at a logical [los] low so that the MOSFET M3 is in the diode chain because the MOSFET M4 is off. The non-test condition of EN2 may be at a logical high so that the MOSFET M5 is essentially shorted out of the diode chain because the MOSFET M6 is on. Therefore, the voltage level of the substrate at node Vbb, under non-test conditions, is substantially equivalent to the supply voltage level Vcc,

less the voltage dropped by the three MOSFETs M1, M2 and M3. Under test conditions, the voltage level at node Vbb can be made more positive by raising the control signal EN1 to a logical high. Such an enabling of the control signal EN1 turns on the MOSFET M4 which essentially shorts the channel of the MOSFET M3 thereby removing the MOSFET M3 from the diode chain, so that the voltage level at Vbb is substantially equivalent to the supply voltage level Vcc, less the voltage dropped by only the MOSFETs M1 and M2. The normal substrate voltage level at Vbb can then be restored by returning the control voltage EN1 to a logical low.

The paragraph beginning on page 6, line 16, is amended as follows:

The addition of the MOSFETs M7, M8, M9 and M10 to the circuit increases the adjustability of the substrate voltage level Vbb, beyond that of the circuit shown in Figure 1. For example, the non-test condition for the control signals EN1 and EN2 may be a logical [los] low so that the MOSFETs M3 and M5 are in the diode chain. The non-test condition for the control signals EN3 and EN4 may be a logical high so that the MOSFETs M7 and M8 are essentially shorted out of the diode chain. Under test conditions, the substrate voltage level Vbb may be made more positive by raising the control signal EN1 to a logical high and essentially shorting the MOSFET M3 out of the diode chain. The substrate voltage level Vbb can then be made even more positive by raising the control signal EN2 to a logical high and essentially shorting the MOSFET M5 out of the diode chain, as well. The normal substrate voltage level at Vbb can then be restored by returning the control signals EN1 And EN2 to a logical low. The substrate voltage level Vbb, can be made more negative from its non-test condition by lowering the control signal EN3 to a logical low and thereby adding the MOSFET M7 to the diode chain. The substrate voltage level Vbb, can then be made even more negative by lowering the control signal EN4 to a logical low and adding the MOSFET M9 to the diode chain.

IN THE CLAIMS

Please cancel claims 1-18 after adding the following new claims:

19. (New)A dynamic random access memory (DRAM), comprising:

an array of memory cells formed on an integrated circuit substrate; and

a substrate voltage regulator circuit coupled to the integrated circuit substrate for setting a substrate voltage bias level.

20. (New)The DRAM of claim 19, wherein the substrate voltage regulator circuit comprises:

a series of diodes coupled between a supply voltage source and the integrated circuit substrate, and at least one bypass transistor coupled to at least one diode in the series of diodes for electrically bypassing the one diode.

21. (New)The DRAM of claim 19, wherein each diode of the series of diodes has a junction voltage drop, and the substrate voltage bias level is defined by a supply voltage level minus junction voltage drops of unbypassed diodes of the series of diodes.

22. (New) A dynamic random access memory (DRAM), comprising:

an array of memory cells formed on a substrate;

a number of wordlines and a number of bitlines coupled to the array of memory cells;

a substrate voltage regulator circuit coupled to the substrate for setting a substrate voltage bias level;

wherein the substrate voltage regulator circuit comprises a series of diodes coupled between a supply voltage source and the substrate; and

wherein the substrate voltage regulator circuit comprises at least one bypass transistor coupled to at least one diode in the series of diodes for electrically bypassing at least one diode.

23. (New) The DRAM of claim 22 wherein the substrate voltage regulator circuit includes a plurality of bypass transistors, each one of the plurality of bypass transistors coupled to at least one diode in the series of diodes for electrically bypassing a plurality of diodes.

24. (New) The DRAM of claim 22 wherein at least one bypass transistor is coupled to a plurality of diodes in the series of diodes for electrically bypassing the plurality of diodes.

25. (New) The DRAM of claim 22 wherein the at least one bypass transistor is turned off during normal operation of the integrated circuit such that at least one diode is unbypassed during normal operation but can be selectively bypassed during testing operations.

26. (New) The DRAM of claim 22 wherein the at least one bypass transistor is turned on during normal operation of the integrated circuit such that at least one diode is bypassed during normal operation but can be selectively unbypassed during testing operations.

27. (New) A dynamic random access memory (DRAM), comprising:

an array of memory cells formed on a substrate;

a number of wordlines and a number of bitlines coupled to the array of memory cells;

a substrate voltage regulator circuit coupled to the substrate for setting a substrate voltage bias level;

wherein the substrate voltage regulator circuit comprises a series of diodes coupled between a supply voltage source and the substrate; and

wherein the substrate voltage regulator circuit comprises at least one bypass transistor coupled to a plurality of diodes in the series of diodes for electrically bypassing the plurality of diodes.

28. (New) The DRAM of claim 27 wherein the at least one bypass transistor is turned off during normal operation of the integrated circuit such that at least one diode is unbypassed during

normal operation but can be selectively bypassed during testing operations.

29. (New) The DRAM of claim 27 wherein the at least one bypass transistor is turned on during normal operation of the integrated circuit such that at least one diode is bypassed during normal operation but can be selectively unbypassed during testing operations.

30. (New) A dynamic random access memory (DRAM), comprising:

an array of memory cells formed on a substrate;

a number of wordlines and a number of bitlines coupled to the array of memory cells;

a substrate voltage regulator circuit coupled to the substrate for setting a substrate voltage bias level;

wherein the substrate voltage regulator circuit comprises a series of diodes coupled between a supply voltage source and the substrate; and

wherein the substrate voltage regulator circuit comprises a plurality of bypass transistors coupled to a plurality of diodes in the series of diodes for electrically bypassing the plurality of diodes.

31. (New) The DRAM of claim 30 wherein the at least one bypass transistor is turned off during normal operation of the integrated circuit such that at least one diode is unbypassed during normal operation but can be selectively bypassed during testing operations.

32. (New) The DRAM of claim 30 wherein the at least one bypass transistor is turned on during normal operation of the integrated circuit such that at least one diode is bypassed during normal operation but can be selectively unbypassed during testing operations.

33. (New) A dynamic random access memory (DRAM), comprising:

an array of memory cells formed on a substrate;

a number of wordlines and a number of bitlines coupled to the array of memory

cells;

a substrate voltage regulator circuit coupled to the substrate for setting a substrate voltage bias level, the substrate voltage regulator circuit comprising a series of diode connected transistors coupled between a supply voltage source and the substrate, and at least one bypass transistor coupled to at least one diode connected transistor in the series of diode connected transistors for electrically bypassing at least one diode connected transistor,

each diode connected transistor of the series of diode connected transistors has a junction voltage drop, and the substrate voltage bias level is defined by a supply voltage level minus junction voltage drops of unbypassed diode connected transistors of the series of diode connected transistors.

34. (New) The DRAM of claim 33 wherein the at least one bypass transistor is coupled to a plurality of diode connected transistors in the series of diode connected transistors for electrically bypassing the plurality of diode connected transistors.

35. (New) The DRAM of claim 33 wherein the at least one bypass transistor is turned off during normal operation of the integrated circuit such that at least one diode is unbypassed during normal operation but can be selectively bypassed during testing operations.

36. (New) The DRAM of claim 33 wherein the at least one bypass transistor is turned on during normal operation of the integrated circuit such that at least one diode is bypassed during normal operation but can be selectively unbypassed during testing operations.

37. (New) A dynamic random access memory (DRAM), comprising:

an array of memory cells formed on a substrate;

a number of wordlines and a number of bitlines coupled to the array of memory cells;

a substrate voltage regulator circuit coupled to the substrate for setting a substrate

voltage bias level, the substrate voltage regulator circuit comprising a series of diode connected transistors coupled between a supply voltage source and the substrate, and at least one bypass transistor coupled to a plurality of diode connected transistors in the series of diode connected transistors for electrically bypassing the plurality of diode connected transistors,

each diode connected transistor of the series of diode connected transistors has a junction voltage drop, and the substrate voltage bias level is defined by a supply voltage level minus junction voltage drops of unbypassed diode connected transistors of the series of diode connected transistors.

38. (New) The DRAM of claim 37 wherein the substrate voltage regulator circuit includes a plurality of bypass transistors, each one of the plurality of bypass transistors coupled to at least one diode connected transistor in the series of diode connected transistors for electrically bypassing a plurality of diode connected transistors.

39. (New) The DRAM of claim 37 wherein the at least one bypass transistor is turned off during normal operation of the integrated circuit memory device such that the one diode connected transistor is unbypassed during normal operation but can be selectively bypassed during testing operations.

40. (New) The DRAM of claim 37 wherein the at least one bypass transistor is turned on during normal operation of the integrated circuit memory device such that the one diode connected transistor is bypassed during normal operation but can be selectively unbypassed during testing operations.

41. (New) A dynamic random access memory (DRAM), comprising:

an array of memory cells formed on a substrate;

a number of wordlines and a number of bitlines coupled to the array of memory cells;

a substrate voltage regulator circuit coupled to the substrate for setting a substrate voltage bias level, the substrate voltage regulator circuit comprising a series of diode connected transistors coupled between a supply voltage source and the substrate, and a plurality of bypass transistors coupled to a plurality of diode connected transistors in the series of diode connected transistors for electrically bypassing the plurality of diode connected transistors,

each diode connected transistor of the series of diode connected transistors has a junction voltage drop, and the substrate voltage bias level is defined by a supply voltage level minus junction voltage drops of unbypassed diode connected transistors of the series of diode connected transistors.

42. (New) The DRAM of claim 41 wherein the plurality of bypass transistors is turned off during normal operation of the integrated circuit memory device such that the one diode connected transistor is unbypassed during normal operation but can be selectively bypassed during testing operations.

43. (New) The DRAM of claim 41 wherein the plurality of bypass transistors is turned on during normal operation of the integrated circuit memory device such that the one diode connected transistor is bypassed during normal operation but can be selectively unbypassed during testing operations.

REMARKS

Claims 1 - 18 have been canceled and new claims 19 - 43 have been added. Claims 19 - 43 are now pending in this application.

The specification is amended to add a cross reference to the prior application. No new matter is added by way of these amendments.

The application filing fee as calculated on the application transmittal sheet reflects the amendments to the claims described above.

The Applicant respectfully requests that the preliminary amendment described herein be entered into the record prior to examination and consideration of the above-identified application.

Respectfully submitted,

GARY R. GILLIAM

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This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to The Commissioner for Patents, Box Patent Application, Washington, D.C. 20231.

Docket No. 00303.221US4 Micron Ref. No. 94-0108.03
WD #

Clean Version of the Amended Specification Paragraphs

ON-CHIP SUBSTRATE REGULATOR TEST MODE
Applicant: Gary R. Gilliam
Serial No.: Unknown

Please replace the paragraph beginning on page 4, line 19, with the following:

For example, in Figure 1, the non-test condition of EN1 may be at a logical low so that the MOSFET M3 is in the diode chain because the MOSFET M4 is off. The non-test condition of EN2 may be at a logical high so that the MOSFET M5 is essentially shorted out of the diode chain because the MOSFET M6 is on. Therefore, the voltage level of the substrate at node Vbb, under non-test conditions, is substantially equivalent to the supply voltage level Vcc, less the voltage dropped by the three MOSFETs M1, M2 and M3. Under test conditions, the voltage level at node Vbb can be made more positive by raising the control signal EN1 to a logical high. Such an enabling of the control signal EN1 turns on the MOSFET M4 which essentially shorts the channel of the MOSFET M3 thereby removing the MOSFET M3 from the diode chain, so that the voltage level at Vbb is substantially equivalent to the supply voltage level Vcc, less the voltage dropped by only the MOSFETs M1 and M2. The normal substrate voltage level at Vbb can then be restored by returning the control voltage EN1 to a logical low.

Please replace the paragraph beginning on page 6, line 16, with the following:

The addition of the MOSFETs M7, M8, M9 and M10 to the circuit increases the adjustability of the substrate voltage level Vbb, beyond that of the circuit shown in Figure 1. For example, the non-test condition for the control signals EN1 and EN2 may be a logical low so that the MOSFETs M3 and M5 are in the diode chain. The non-test condition for the control signals EN3 and EN4 may be a logical high so that the MOSFETs M7 and M8 are essentially shorted out of the diode chain. Under test conditions, the substrate voltage level Vbb may be made more positive by raising the control signal EN1 to a logical high and essentially shorting the MOSFET M3 out of the diode chain. The substrate voltage level Vbb can then be made even more positive

by raising the control signal EN2 to a logical high and essentially shorting the MOSFET M5 out of the diode chain, as well. The normal substrate voltage level at Vbb can then be restored by returning the control signals EN1 And EN2 to a logical low. The substrate voltage level Vbb, can be made more negative from its non-test condition by lowering the control signal EN3 to a logical low and thereby adding the MOSFET M7 to the diode chain. The substrate voltage level Vbb, can then be made even more negative by lowering the control signal EN4 to a logical low and adding the MOSFET M9 to the diode chain.